

- Advanced Process Technology
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Ease of Paralleling
- Simple Drive Requirements

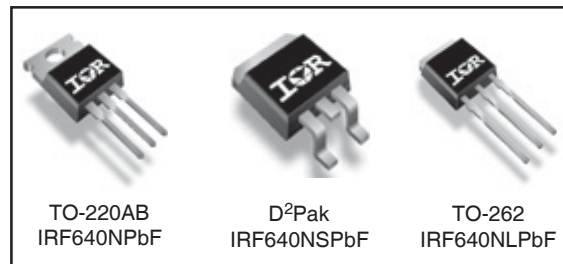
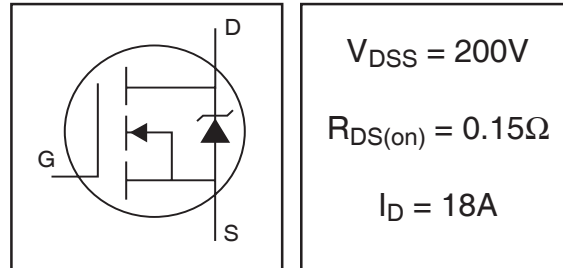
Lead-Free Description

Fifth Generation HEXFET® Power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The TO-220 package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 watts. The low thermal resistance and low package cost of the TO-220 contribute to its wide acceptance throughout the industry.

The D²Pak is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D²Pak is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0W in a typical surface mount application.

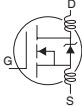
The through-hole version (IRF640NL) is available for low-profile application.



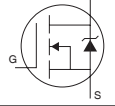
Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	18	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	13	
I_{DM}	Pulsed Drain Current ①	72	
$P_D @ T_C = 25^\circ C$	Power Dissipation	150	W
	Linear Derating Factor	1.0	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy②	247	mJ
I_{AR}	Avalanche Current①	18	A
E_{AR}	Repetitive Avalanche Energy①	15	mJ
dv/dt	Peak Diode Recovery dv/dt ③	8.1	V/ns
T_J	Operating Junction and	-55 to +175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting torque, 6-32 or M3 srew④	10 lbf•in (1.1N•m)	

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	200	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔV _{(BR)DSS/ΔT_J}	Breakdown Voltage Temp. Coefficient	—	0.25	—	V/°C	Reference to 25°C, I _D = 1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	—	0.15	Ω	V _{GS} = 10V, I _D = 11A ③
V _{GS(th)}	Gate Threshold Voltage	2.0	—	4.0	V	V _{DS} = V _{GS} , I _D = 250μA
g _{fs}	Forward Transconductance	6.8	—	—	S	V _{DS} = 50V, I _D = 11A ③
I _{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	V _{DS} = 200V, V _{GS} = 0V
		—	—	250		V _{DS} = 160V, V _{GS} = 0V, T _J = 150°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V _{GS} = -20V
Q _g	Total Gate Charge	—	—	67	nC	I _D = 11A
Q _{gs}	Gate-to-Source Charge	—	—	11		V _{DS} = 160V
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	—	33		V _{GS} = 10V, See Fig. 6 and 13
t _{d(on)}	Turn-On Delay Time	—	10	—	ns	V _{DD} = 100V
t _r	Rise Time	—	19	—		I _D = 11A
t _{d(off)}	Turn-Off Delay Time	—	23	—		R _G = 2.5Ω
t _f	Fall Time	—	5.5	—		R _D = 9.0Ω, See Fig. 10 ③
L _D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L _S	Internal Source Inductance	—	7.5	—		
C _{iss}	Input Capacitance	—	1160	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	185	—		V _{DS} = 25V
C _{rss}	Reverse Transfer Capacitance	—	53	—		f = 1.0MHz, See Fig. 5

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	18	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode)①	—	—	72		
V _{SD}	Diode Forward Voltage	—	—	1.3	V	T _J = 25°C, I _S = 11A, V _{GS} = 0V ③
t _{rr}	Reverse Recovery Time	—	167	251	ns	T _J = 25°C, I _F = 11A
Q _{rr}	Reverse Recovery Charge	—	929	1394	nC	di/dt = 100A/μs ③
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L _S +L _D)				

Thermal Resistance

	Parameter	Typ.	Max.	Units
R _{θJC}	Junction-to-Case	—	1.0	°C/W
R _{θCS}	Case-to-Sink, Flat, Greased Surface ④	0.50	—	
R _{θJA}	Junction-to-Ambient④	—	62	
R _{θJA}	Junction-to-Ambient (PCB mount)⑤	—	40	

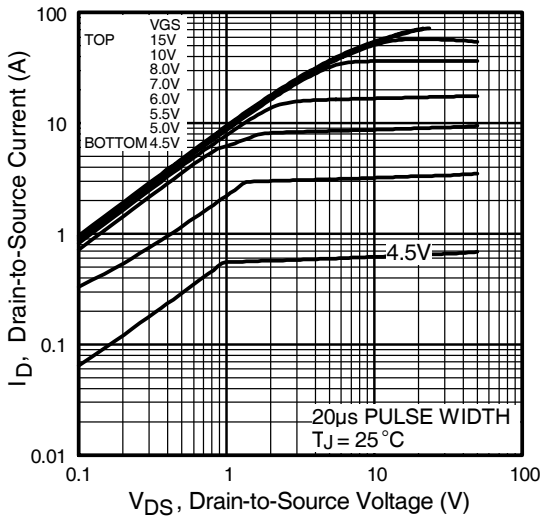


Fig 1. Typical Output Characteristics

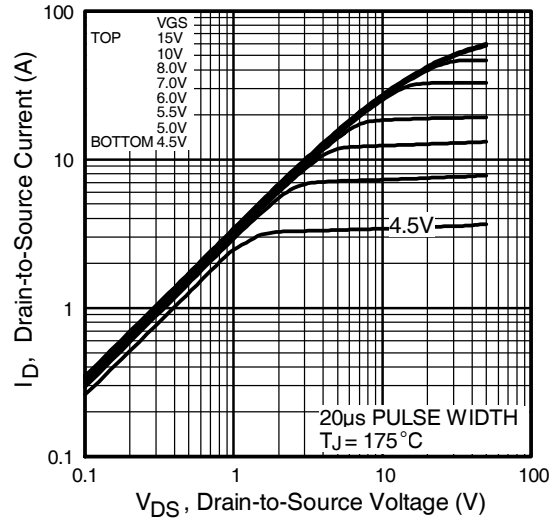


Fig 2. Typical Output Characteristics

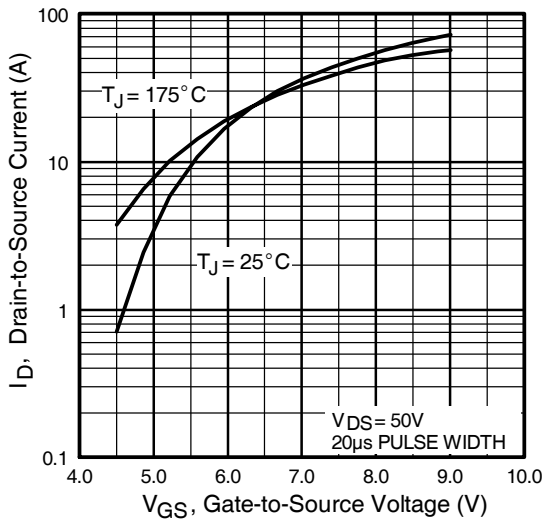


Fig 3. Typical Transfer Characteristics

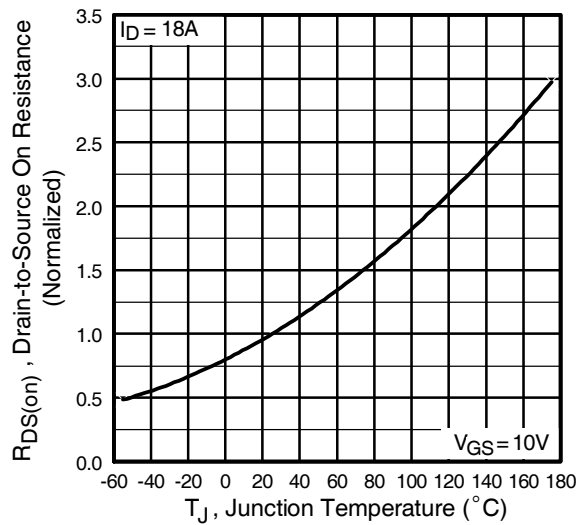


Fig 4. Normalized On-Resistance Vs. Temperature

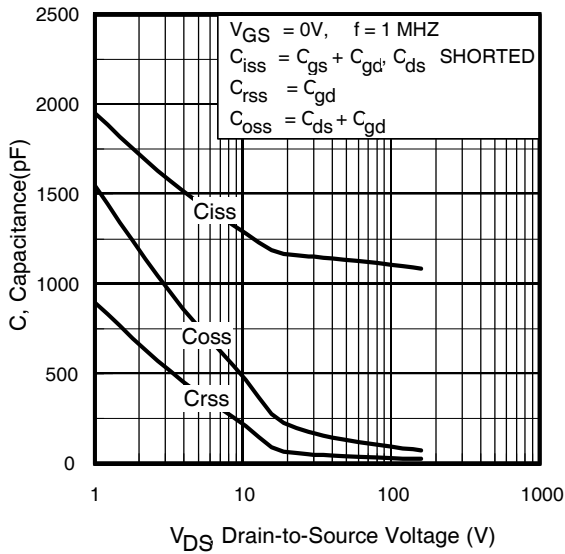


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

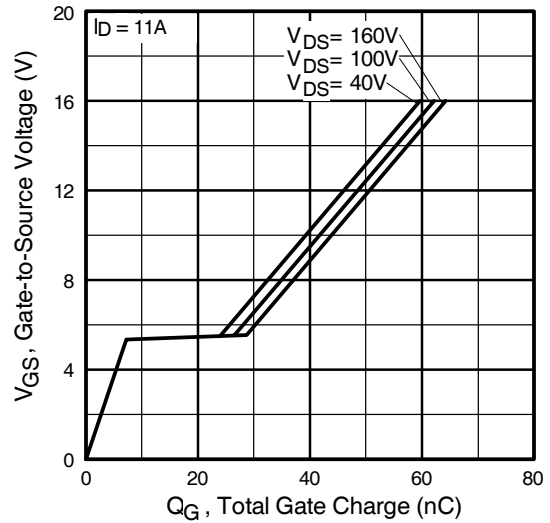


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

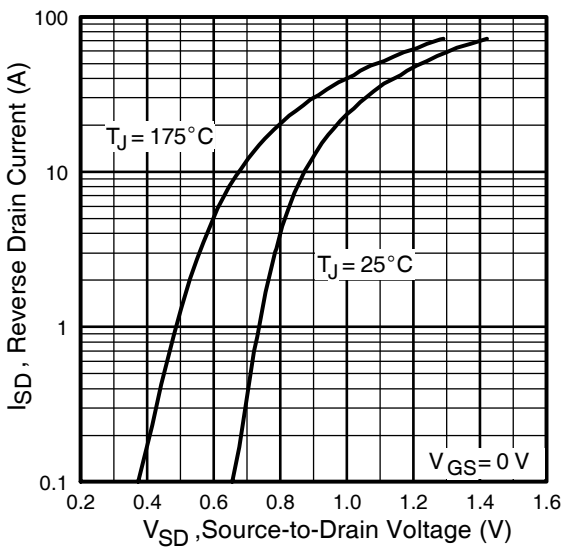


Fig 7. Typical Source-Drain Diode Forward Voltage

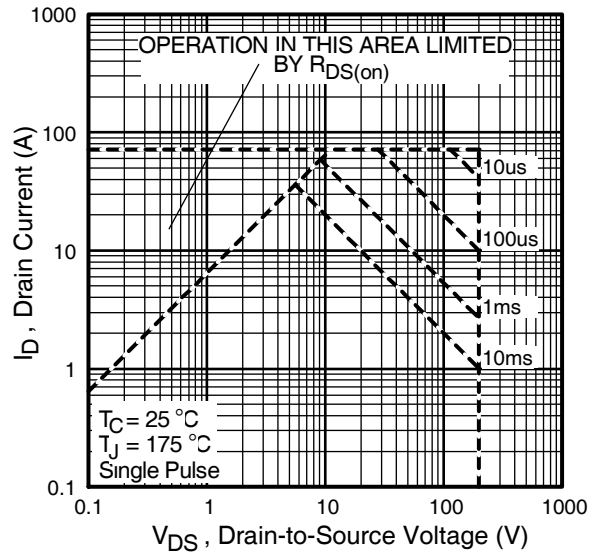


Fig 8. Maximum Safe Operating Area

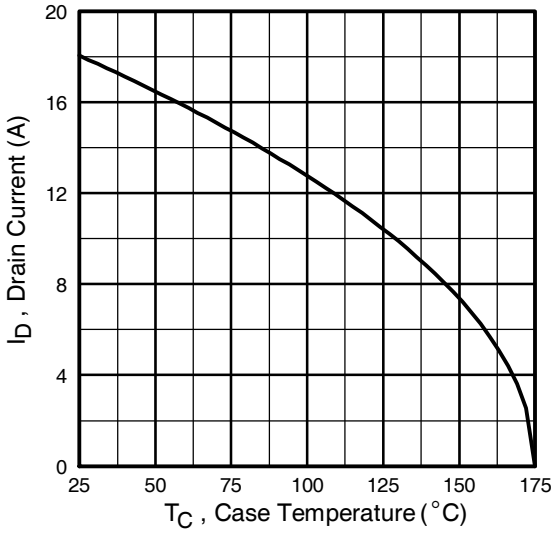


Fig 9. Maximum Drain Current Vs. Case Temperature

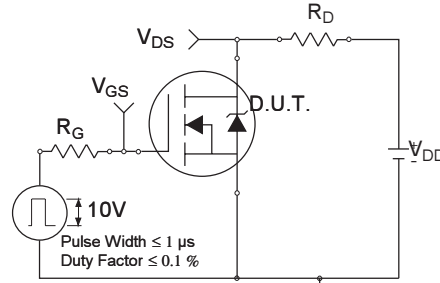


Fig 10a. Switching Time Test Circuit

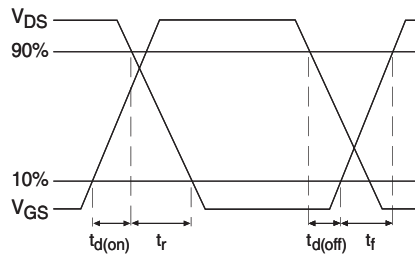


Fig 10b. Switching Time Waveforms

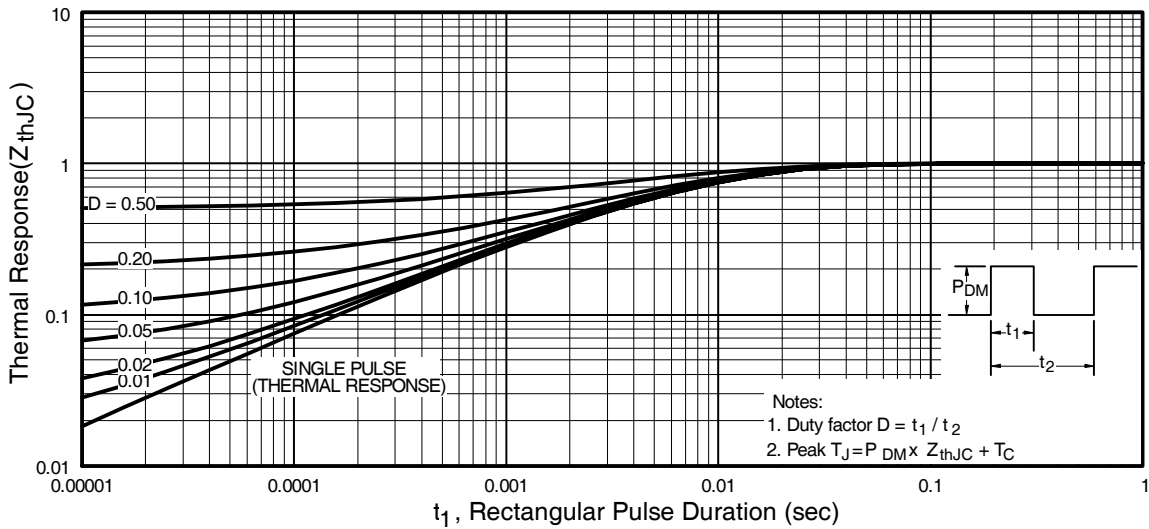


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

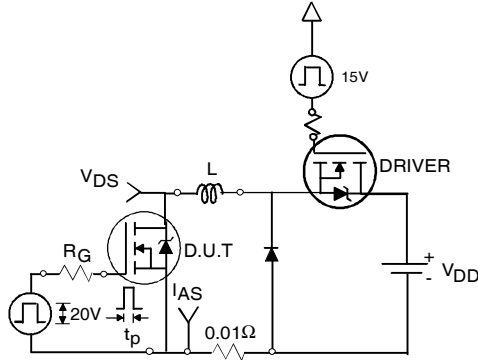


Fig 12a. Unclamped Inductive Test Circuit

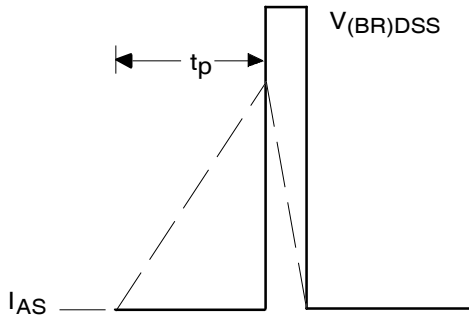


Fig 12b. Unclamped Inductive Waveforms

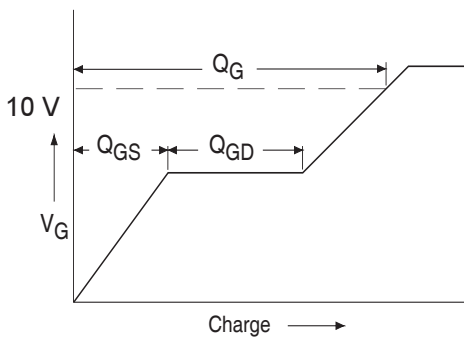


Fig 13a. Basic Gate Charge Waveform

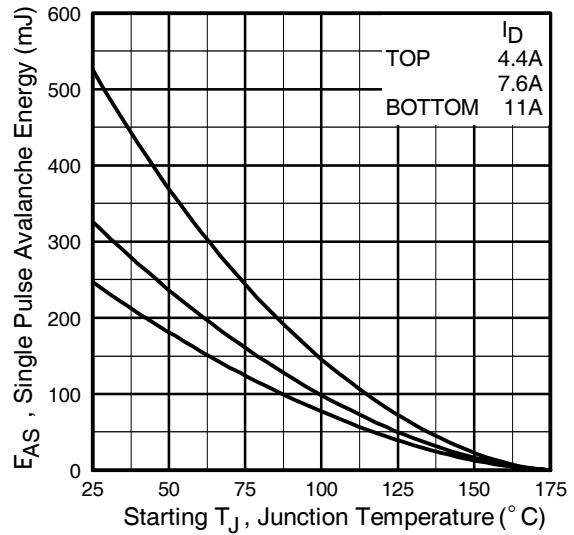


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

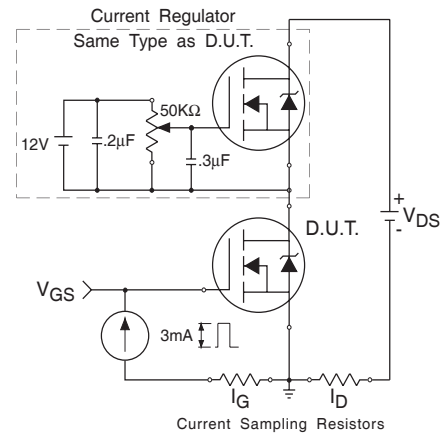
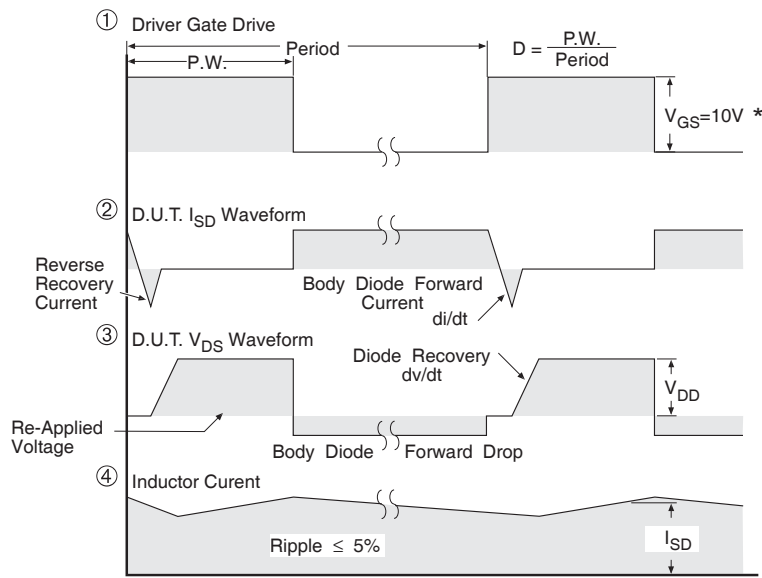
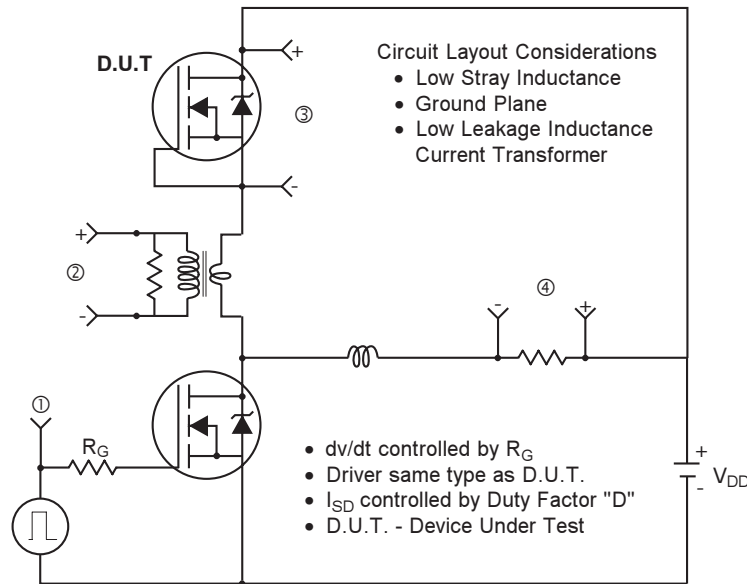


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



* $V_{GS} = 5V$ for Logic Level Devices

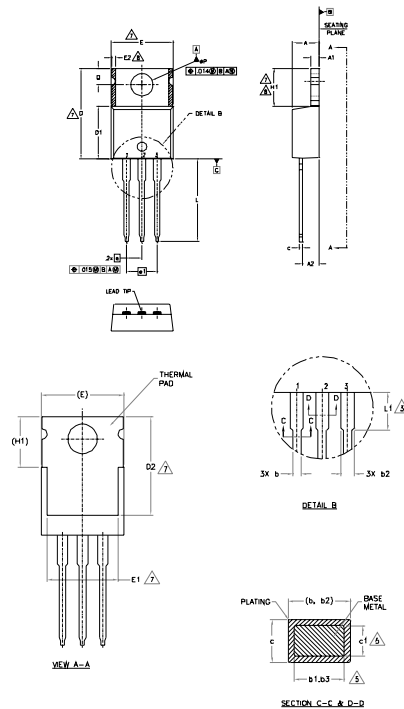
Fig 14. For N-Channel HEXFET® Power MOSFETs

IRF640N/S/LPbF



TO-220AB Package Outline

Dimensions are shown in millimeters (inches)



- NOTES:
- 1.- DIMENSIONING AND TOLERANCING AS PER ASME Y14.5 M-1994.
 - 2.- DIMENSIONS ARE SHOWN IN INCHES (MILLIMETERS).
 - 3.- LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
 - 4.- DIMENSION D, D1 & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
 - 5.- DIMENSION b1, b3 & c1 APPLY TO BASE METAL ONLY.
 - 6.- CONTROLLING DIMENSION 3 INCHES.
 - 7.- THERMAL PAD CONTOUR OPTIONAL. WITHIN DIMENSIONS E, H1, D2 & E1.
 - 8.- DIMENSION E2 x H1 DEFINE A ZONE WHERE STAMPING AND SINGULATION IRREGULARITIES ARE ALLOWED.
 - 9.- OUTLINE CONFORMS TO JEDEC TO-220, EXCEPT A2 (max.) AND D2 (min.) WHERE DIMENSIONS ARE DERIVED FROM THE ACTUAL PACKAGE OUTLINE.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	3.56	4.83	.140	.190	
A1	0.51	1.40	.020	.055	
A2	2.03	2.92	.080	.115	
ø	0.38	1.01	.015	.040	
b1	0.38	0.97	.015	.038	5
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.36	0.61	.014	.024	
c1	0.36	0.56	.014	.022	
D	14.92	16.51	.560	.650	4
D1	8.38	9.02	.330	.365	
D2	11.68	12.88	.460	.507	7
E	9.65	10.67	.380	.420	4,7
E1	6.86	8.89	.270	.350	7
E2	-	0.76	-	.030	8
e	2.54 BSC		.100 BSC		
e1	5.08 BSC		.200 BSC		
H1	5.84	6.86	.230	.270	7,8
L	12.70	14.73	.500	.580	
L1	3.56	4.06	.140	.160	
øP	3.54	4.08	.139	.161	3
Q	2.54	3.42	.100	.135	

LEAD ASSIGNMENTS

- 1- GATE
- 2- DRAIN
- 3- SOURCE

GATE-OUTLINE

- 1- GATE
- 2- COLLECTOR
- 3- EMITTER

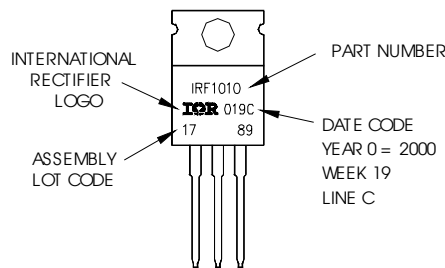
DIODES

- 1- ANODE
- 2- CATHODE
- 3- ANODE

TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010
 LOT CODE 1789
 ASSEMBLED ON WW 19, 2000
 IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position
 indicates "Lead-Free"



TO-220AB package is not recommended for Surface Mount Application

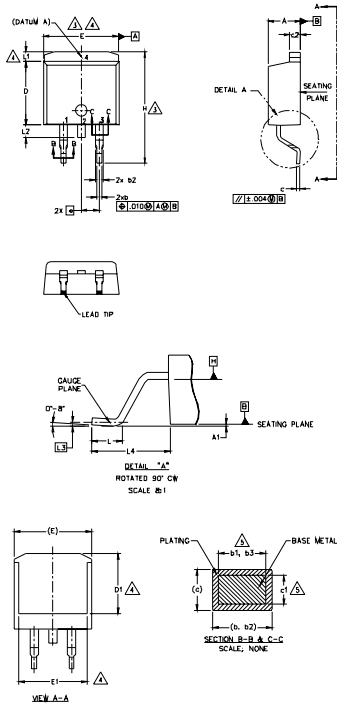
Notes:

1. For an Automotive Qualified version of this part please see <http://www.irf.com/product-info/automotive/>
2. For the most current drawing please refer to IR website at <http://www.irf.com/package/>

www.irf.com

D²Pak (TO-263AB) Package Outline

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1	0.00	0.254	.000	.010	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	5
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.38	0.74	.015	.029	
c1	0.38	0.58	.015	.023	5
c2	1.14	1.65	.045	.065	
D	8.38	9.65	.330	.380	3
D1	6.86	-	.270	-	4
E	9.65	10.67	.380	.420	3,4
E1	6.22	-	.245	-	4
e	2.54 BSC		.100 BSC		
H	14.61	15.88	.575	.625	
L	1.78	2.79	.070	.110	
L1	-	1.65	-	.066	4
L2	-	1.78	-	.070	
L3	0.25 BSC		.010 BSC		
L4	4.78	5.28	.188	.208	

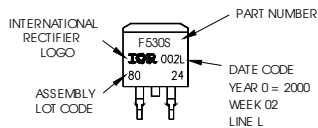
NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
- DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY AT DATUM H.
- THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, L1, D1 & E1.
- DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
- DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
- CONTROLLING DIMENSION: INCH.
- OUTLINE CONFORMS TO JEDEC OUTLINE TO-263AB.

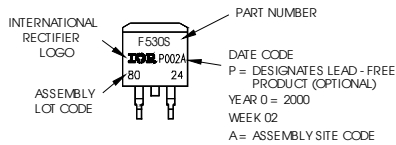
D²Pak (TO-263AB) Part Marking Information

EXAMPLE: THIS IS AN IRF530S WITH
LOT CODE 8024
ASSEMBLED ON WW 02, 2000
IN THE ASSEMBLY LINE "L"

Note: "P" in assembly line position
indicates "Lead - Free"



OR



Notes:

- For an Automotive Qualified version of this part please see <http://www.irf.com/product-info/auto/>
- For the most current drawing please refer to IR website at <http://www.irf.com/package/>

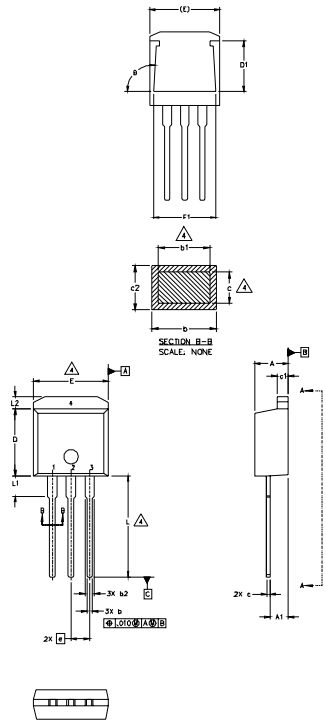
www.irf.com

IRF640N/S/LPbF



TO-262 Package Outline

Dimensions are shown in millimeters (inches)



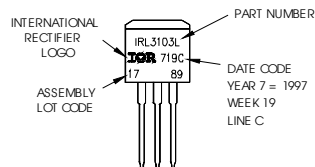
SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1	2.03	2.92	.080	.115	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	4
b2	1.14	1.40	.045	.055	
c	0.38	0.63	.015	.025	4
c1	1.14	1.40	.045	.055	
c2	0.43	.063	.017	.029	
D	8.51	9.65	.335	.380	3
D1	5.33		.210		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
L	13.46	14.09	.530	.555	
L1	3.56	3.71	.140	.146	
L2			1.65	.065	

LEAD ASSIGNMENTS

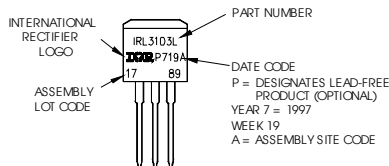
HEXFET	IGBT
1.- GATE	1 - GATE
2.- DRAIN	2 - COLLECTOR
3.- SOURCE	3 - EMITTER
4.- DRAIN	

TO-262 Part Marking Information

EXAMPLE: THIS IS AN IRL3103L
 LOT CODE 1789
 ASSEMBLED ON WW 19, 1997
 IN THE ASSEMBLY LINE "C"
 Note: "P" in assembly line position indicates "Lead-Free"



OR

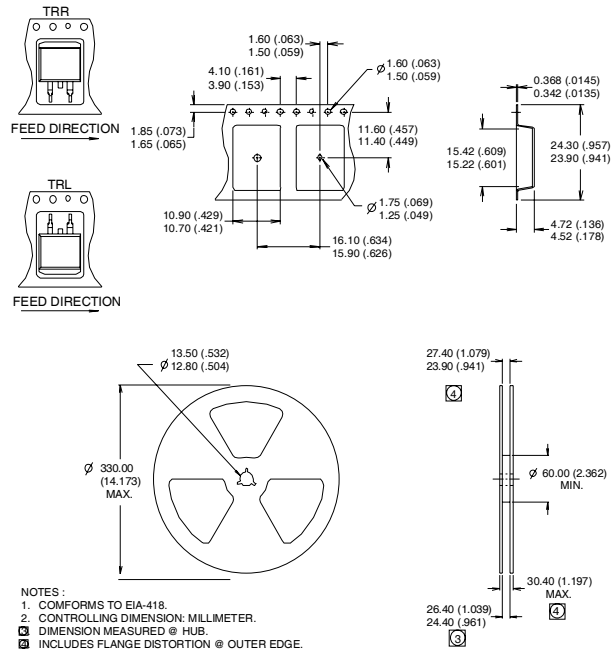


Notes:

1. For an Automotive Qualified version of this part please see <http://www.irf.com/product-info/auto/>
2. For the most current drawing please refer to IR website at <http://www.irf.com/package/>

www.irf.com

D²Pak Tape & Reel Information
 Dimensions are shown in millimeters (inches)



Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 4.2\text{mH}$
 $R_G = 25\Omega$, $I_{AS} = 11\text{A}$.
- ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ This is only applied to TO-220AB package.
- ⑤ This is applied to D²Pak, when mounted on 1" square PCB (FR-4 or G-10 Material).
 For recommended footprint and soldering techniques refer to application note #AN-994.
- ⑥ $I_{SD} \leq 11\text{A}$, $di/dt \leq 344\text{A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$.
 $T_J \leq 175^\circ\text{C}$

Data and specifications subject to change without notice.

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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moschip.ru_9